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DATE: May 2, 2002

SHEET 1\_ of 1\_

Form PTO - 1449 (Modified)

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE  
(Modified) PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

(37 CFR 1.98 (b))

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09/726,860

APPLICANT

E. Morita

FILING DATE

November 30, 2000

GROUP

1765

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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	6 0 5 1 8 4 9	04/18/00	David, et al.			

## FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NUMBER	PUBLIC- ATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANS- LATION	
							YES	NO
		0 9 4 2 4 5 9	15.09.99	EP				
	1	0 3 1 2 9 7 1	24.11.98	JP			*	
	1	1 1 2 6 9 4 8	11.05.99	JP			*	

\*abstract only

## OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

MAA		Zheleva, et al., Pendeco-Epitaxy - A New Approach for Lateral Growth of Gallium Nitride Structures, <i>MRS Internet J. Nitride Semicond. Res.</i> 4S1, G3.38 (1999)
MAA		Thomson, et al., Ranges of Deposition Temperatures Applicable for Metalorganic Vapor Phase Epitaxy of GaN Films Via the Technique of Pendeco-Epitaxy, <i>MRS Internet J. Nitride Semicond. Res.</i> 4S1, G3.37 (1999)
MAA		T. Gehrke, et al., Pendeco-Epitaxy of Gallium Nitride and Aluminum Nitride Films and Heterostructures on Silicon Carbide Substrate, <i>MRS Internet J. Semicond. Res.</i> 4S1, G3.2 (1999)
MAA		K. Linthicum, et al., Process Routes for Low Defect-Density GaN on Various Substrates Employing Pendeco-Epitaxial Growth Techniques, <i>MRS Internet J. Nitride Semicond. Res.</i> 4S1, G4.9 (1999)
MAA		T. Zheleva, et al., Dislocation Density Reduction via Lateral Epitaxy in Selectively Grown GaN Structures, <i>Appl. Phys. Lett.</i> 71 (17), 27 October 1997, pg. 2472
MAA		K. Linthicum, et al., Pendecoepitaxy of Gallium Nitride Thin Films, <i>Appl. Phys. Lett.</i> 75 (2), 1999, pg. 196
MAA		T. Zheleva, et al., Pendeco-Epitaxy: A New Approach for Lateral Growth of Gallium Nitride Films, <i>J. Electronic Materials</i> , 28 (4), 1999, pg. L5

EXAMINER

Matthew Anderson

DATE CONSIDERED

7/15/2002

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

(Form PTO-1449)